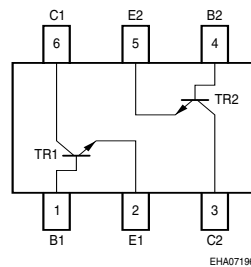
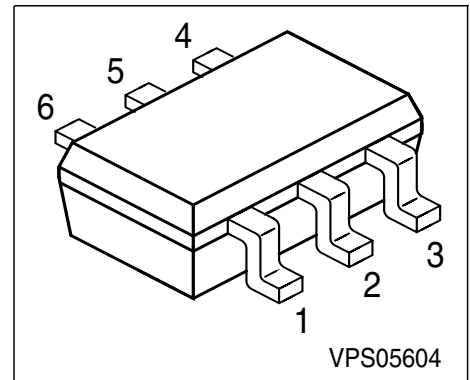


NPN Silicon RF Transistor

- For low-noise, high-gain broadband amplifier at collector currents from 0.5 mA to 12 mA
- $f_T = 8$ GHz
 $F = 1.4$ dB at 900 MHz
- Two (galvanic) internal isolated Transistors in one package



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFS 481	RFs	1=B	2=E	3=C	4=B	5=E	6=C	SOT-363

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	20	mA
Base current	I_B	2	
Total power dissipation, $T_S \leq 83$ °C ¹⁾	P_{tot}	175	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point	R_{thjS}	≤ 380	K/W
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¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}, V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 5\text{ mA}, V_{CE} = 8\text{ V}$	h_{FE}	50	100	200	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

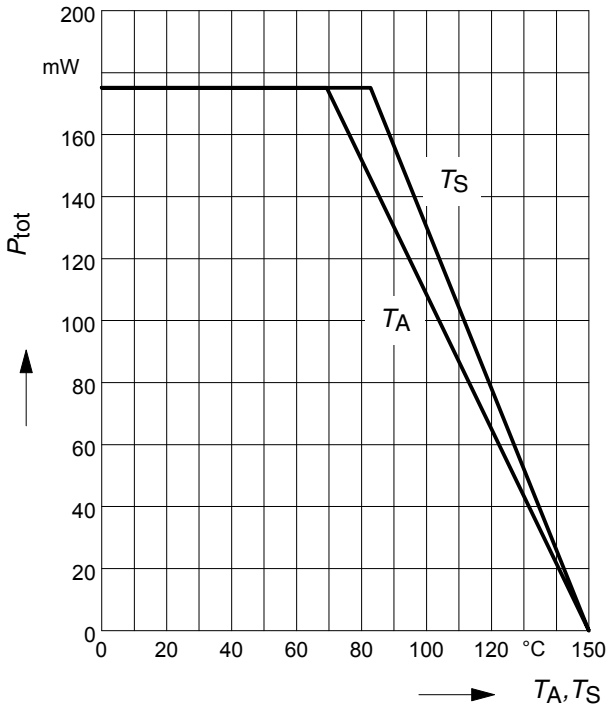
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC characteristics (verified by random sampling)					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	0.24	0.4	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ce}	-	0.11	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	0.35	-	
Noise figure $I_C = 2\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	F	-	1.45 1.8	-	dB
Power gain, maximum stable ^{F)} $I_C = 5\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$	G_{ms}	-	19	-	
Power gain, maximum available ^{F)} $I_C = 5\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ma}	-	14.5	-	
Transducer gain $I_C = 5\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	15.5 10.5	-	

$$^1G_{ms} = |S_{21} / S_{12}|$$

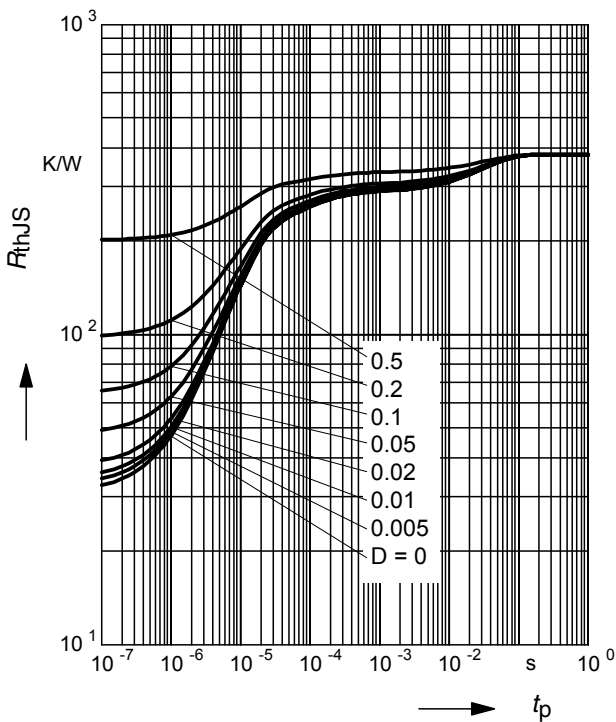
$$^2G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

Total power dissipation $P_{tot} = f(T_A^*, T_S)$

* Package mounted on epoxy

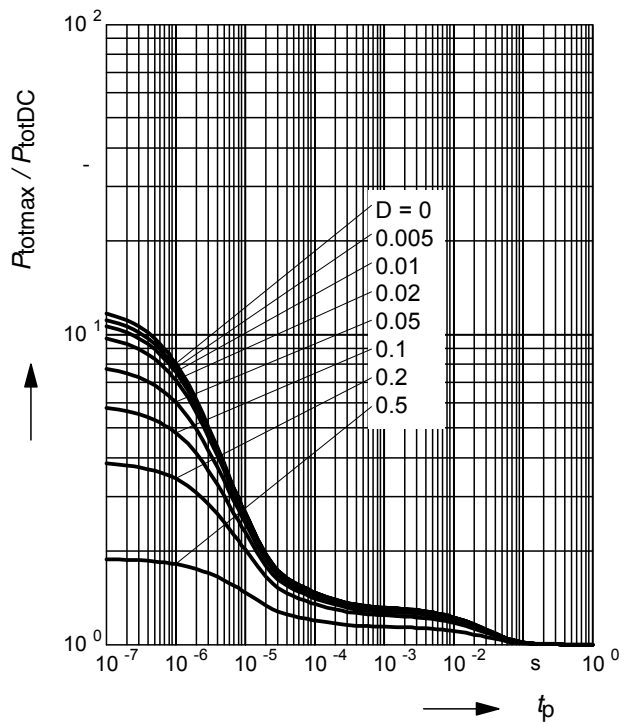


Permissible Pulse Load $R_{thJS} = f(t_p)$



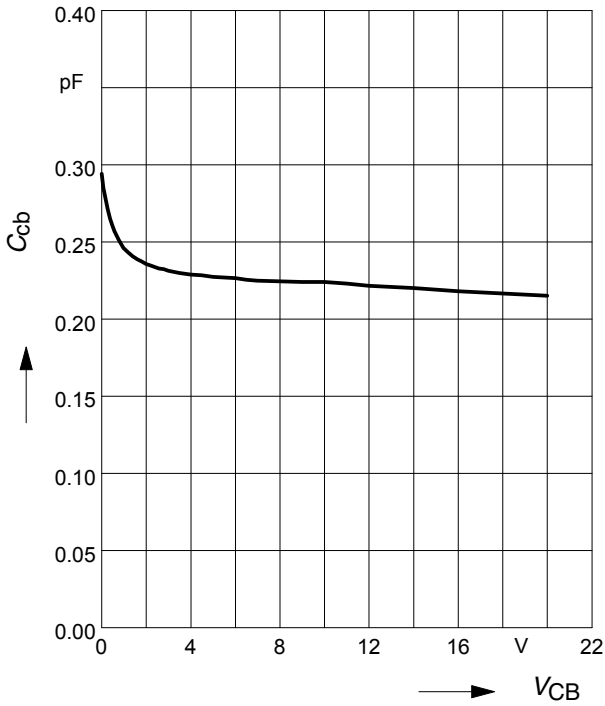
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$



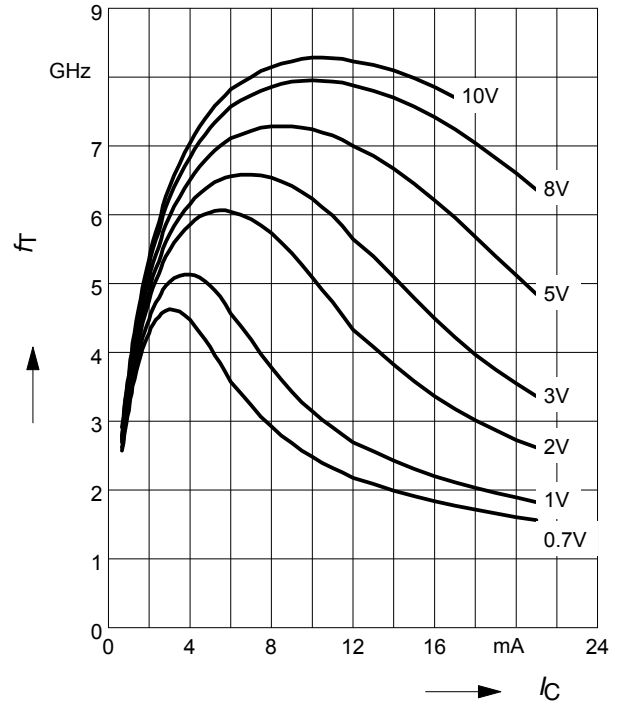
Collector-base capacitance $C_{cb} = f(V_{CB})$

$f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

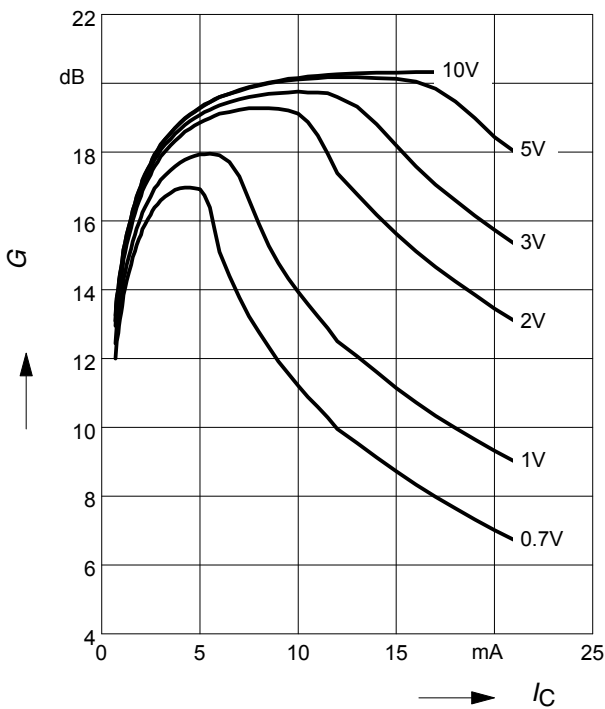
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

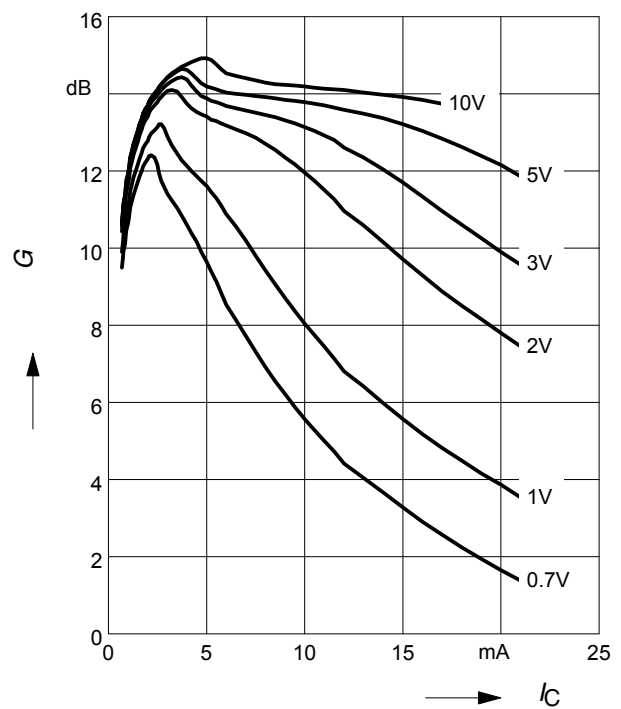
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 1.8\text{GHz}$

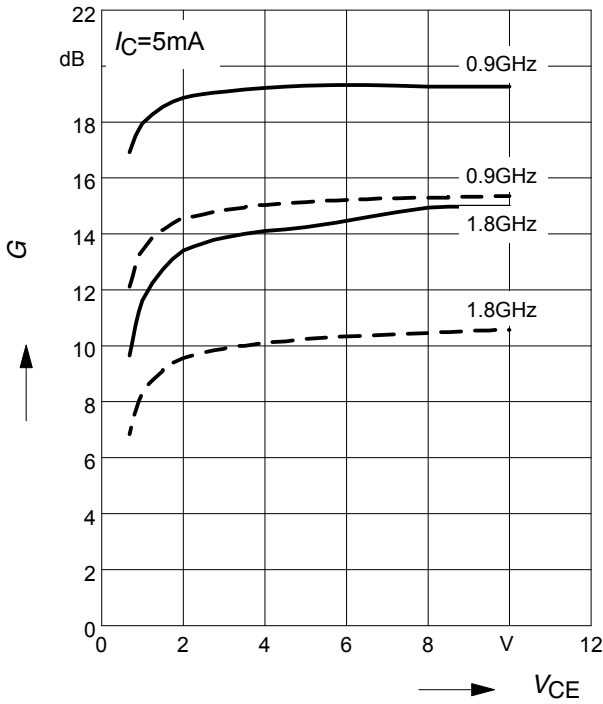
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(V_{CE})$:

$|S_{21}|^2 = f(V_{CE})$:

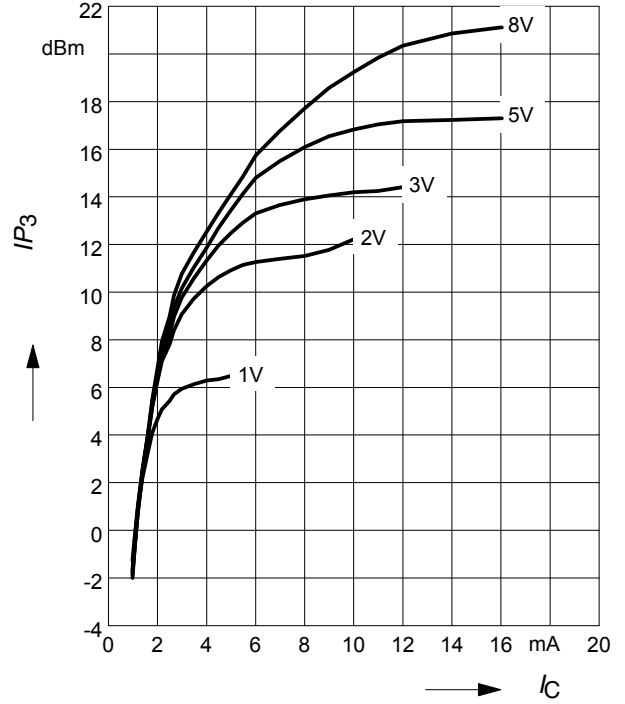
$f =$ Parameter



Intermodulation Intercept Point $IP_3 = f(I_C)$

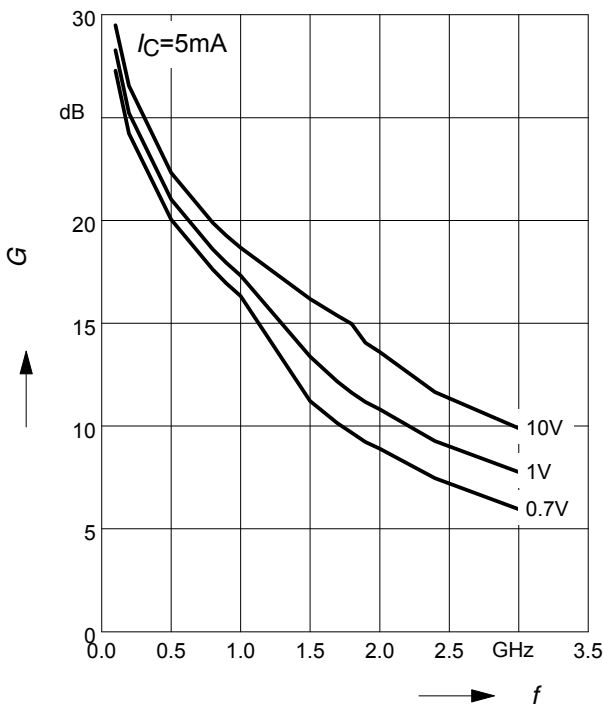
(3rd order, Output, $Z_S = Z_L = 50\Omega$)

$V_{CE} =$ Parameter, $f = 900\text{MHz}$



Power Gain $G_{ma}, G_{ms} = f(f)$

$V_{CE} =$ Parameter



Power Gain $|S_{21}|^2 = f(f)$

$V_{CE} =$ Parameter

